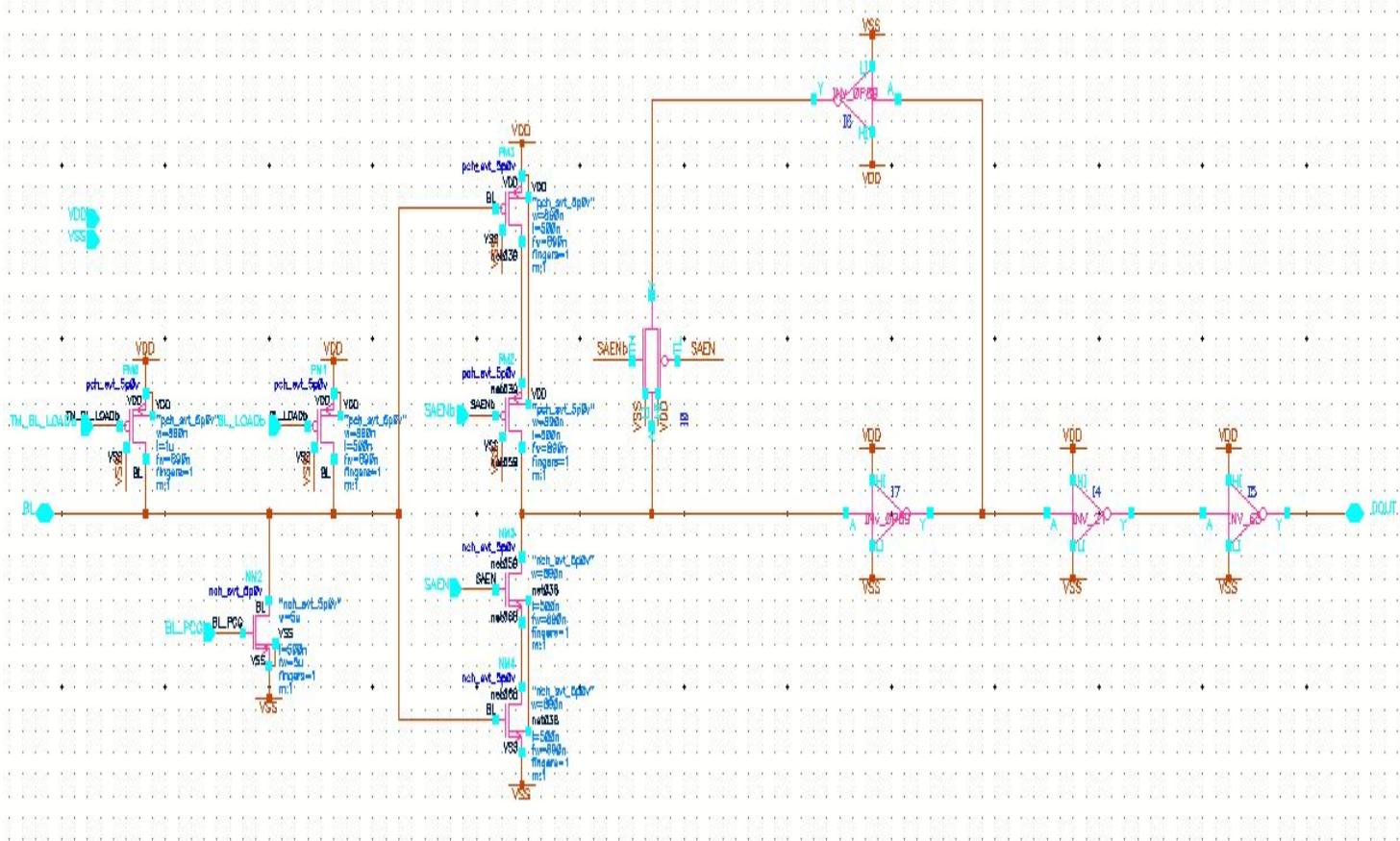
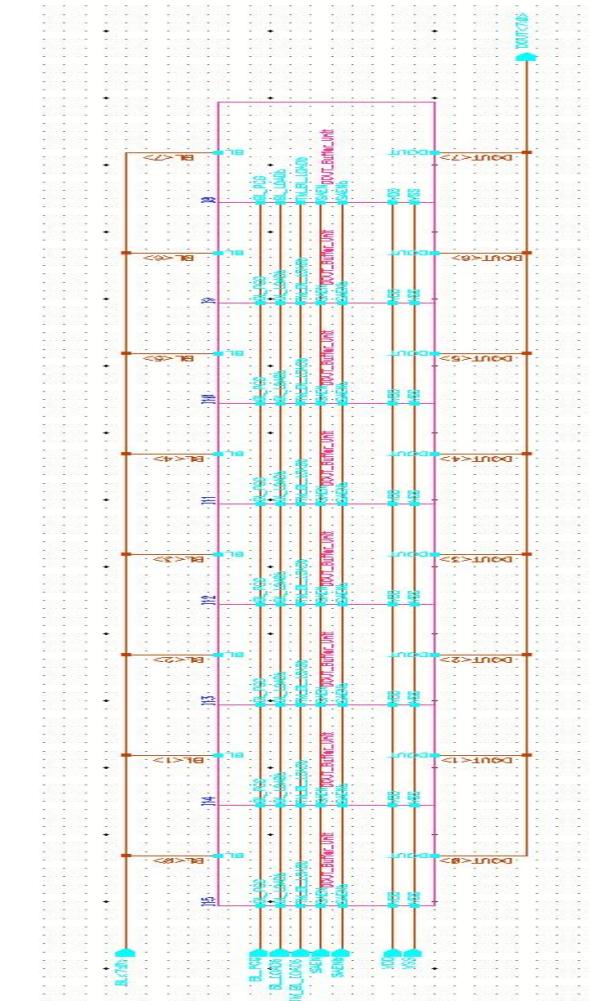


DBHitek 180nm BCD Process eFuse Cell Array _Simulation_Schematic

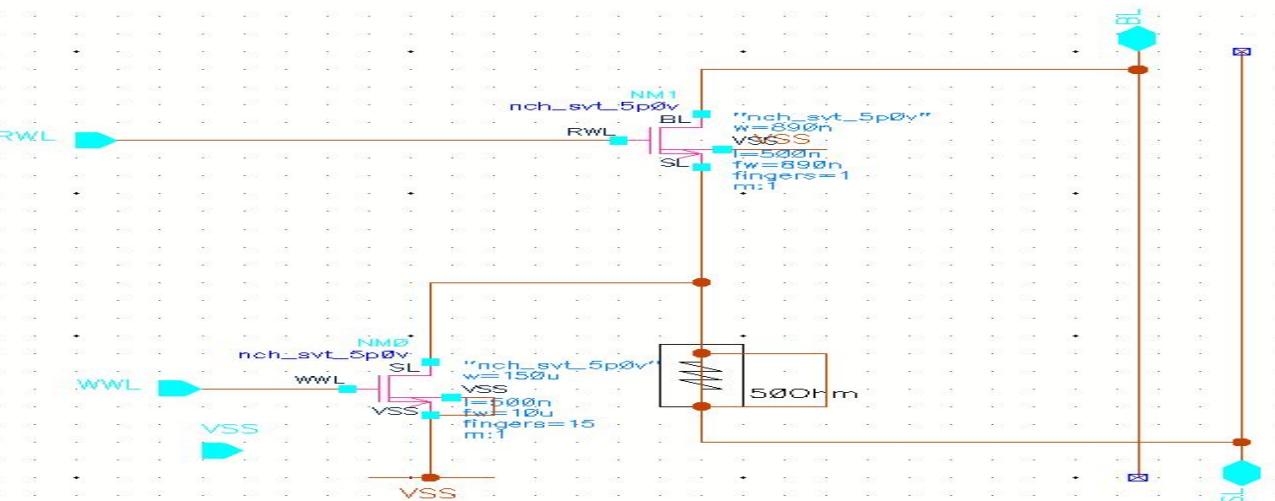


DOUT_Buffer_Unit
_Schematic

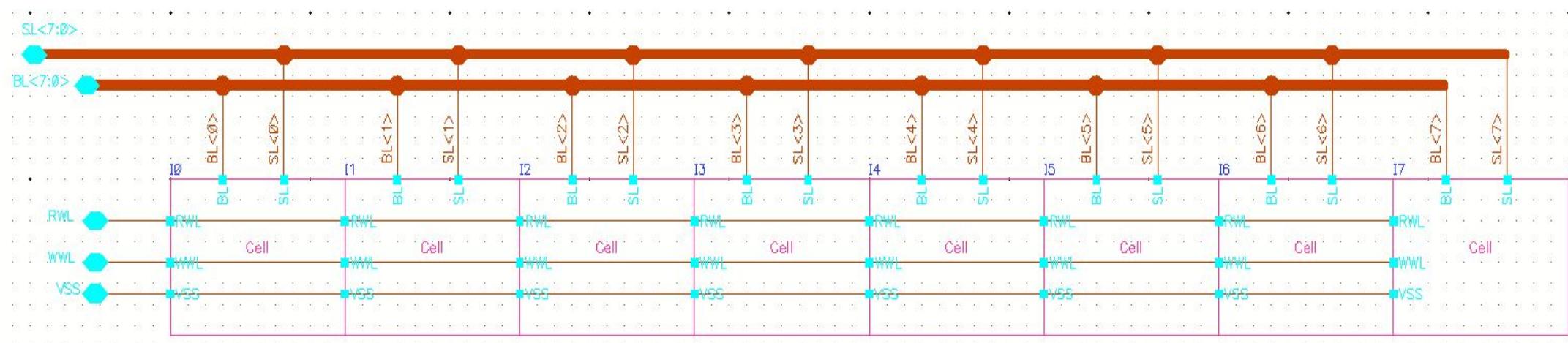


DOUT_Buffer_Unit_8C_Schematic

DBHitek 180nm BCD Process eFuse Cell Array _Simulation_Schematic

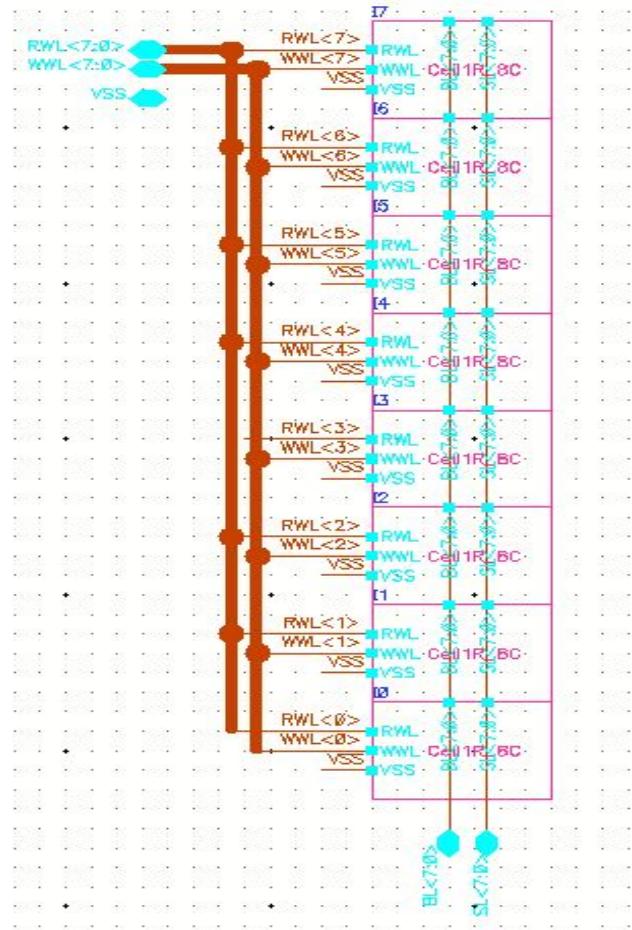


Cell_Schematic
C

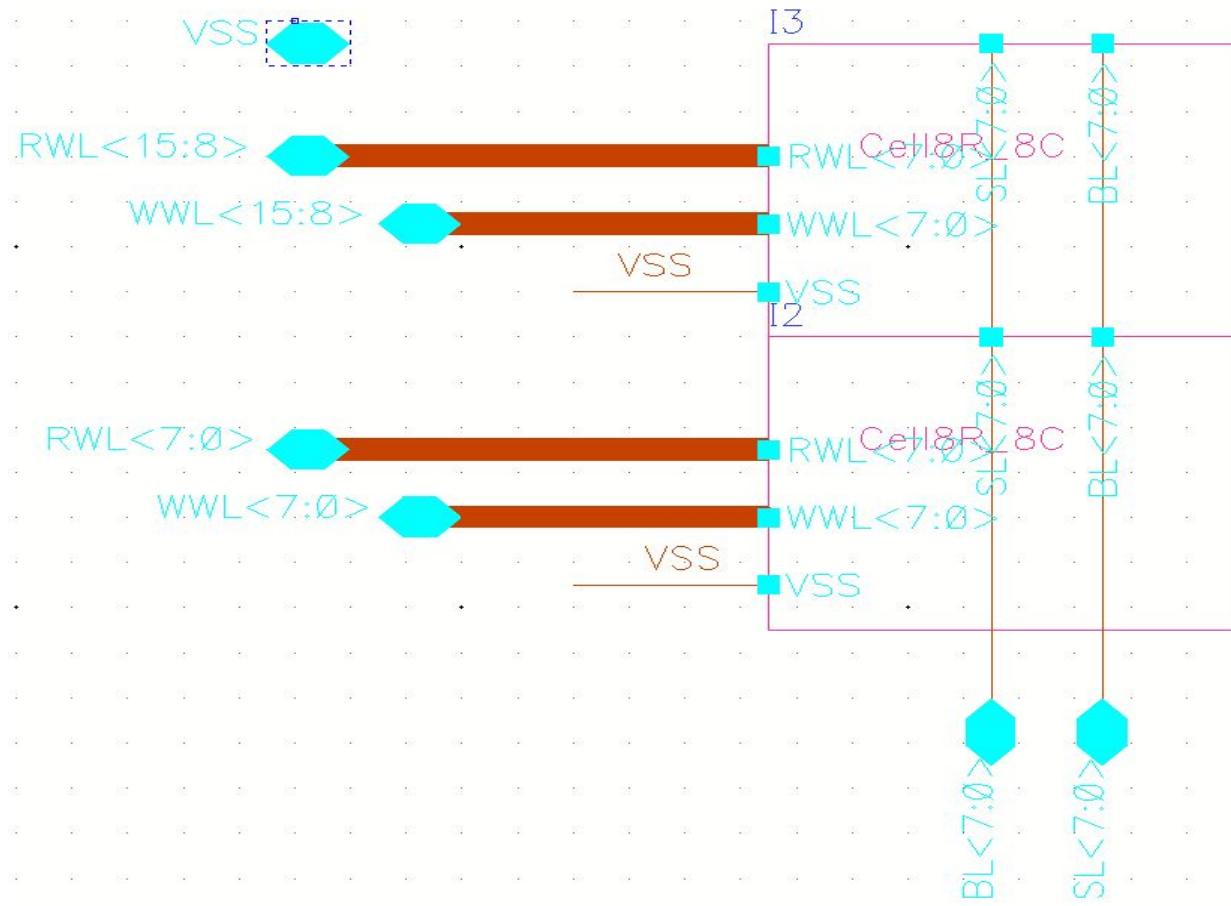


Cell1R_8C_Schematic

DBHitek 180nm BCD Process eFuse Cell Array _Simulation_Schematic

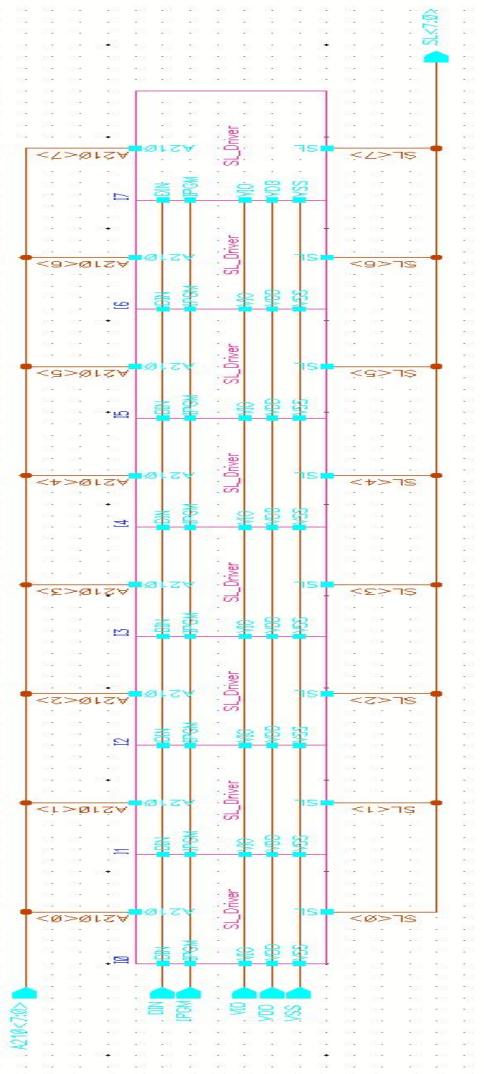


Cell8R_8C_Schematic
c

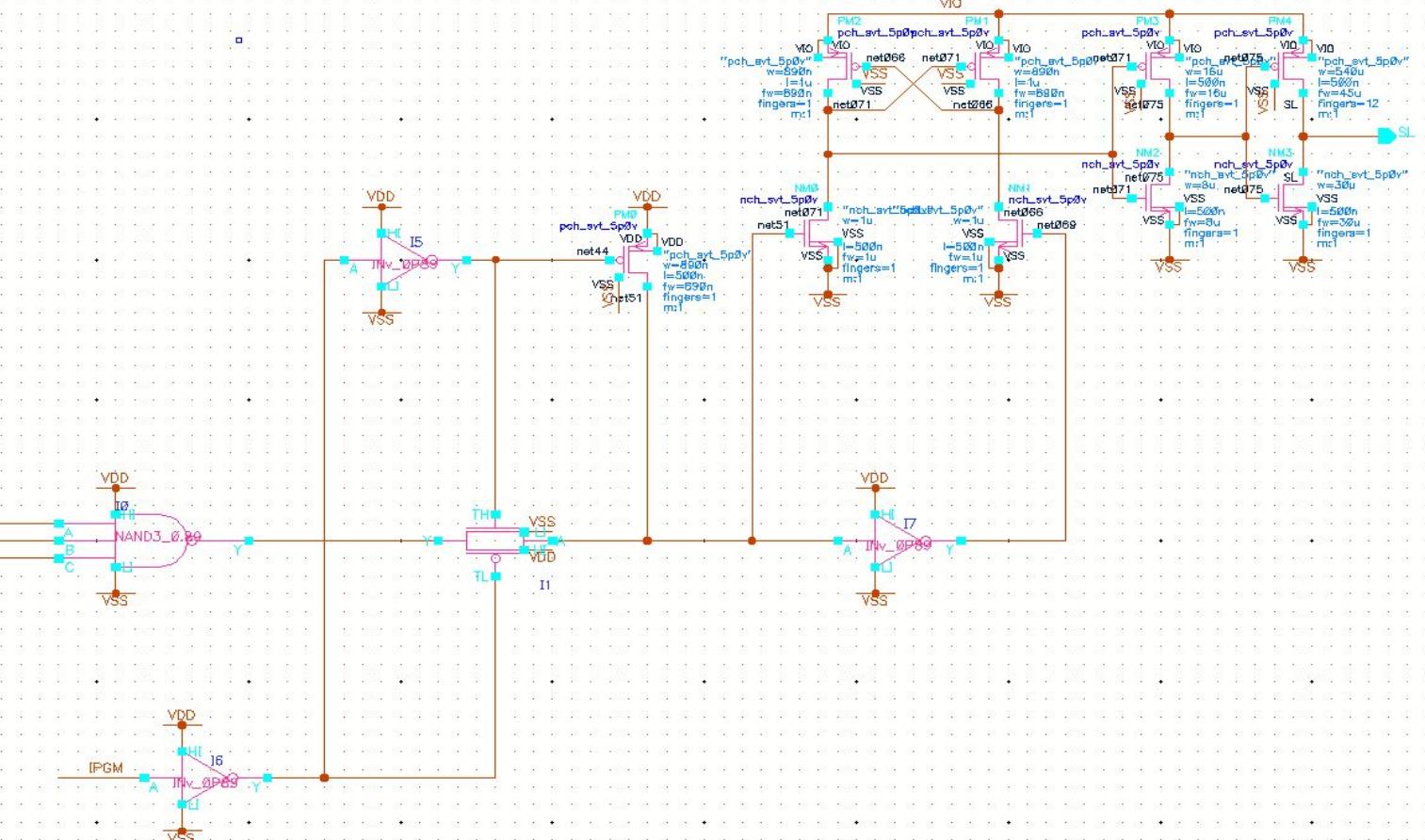


Cell16R_8C_Schematic

DBHitek 180nm BCD Process eFuse Cell Array _Simulation_Schematic

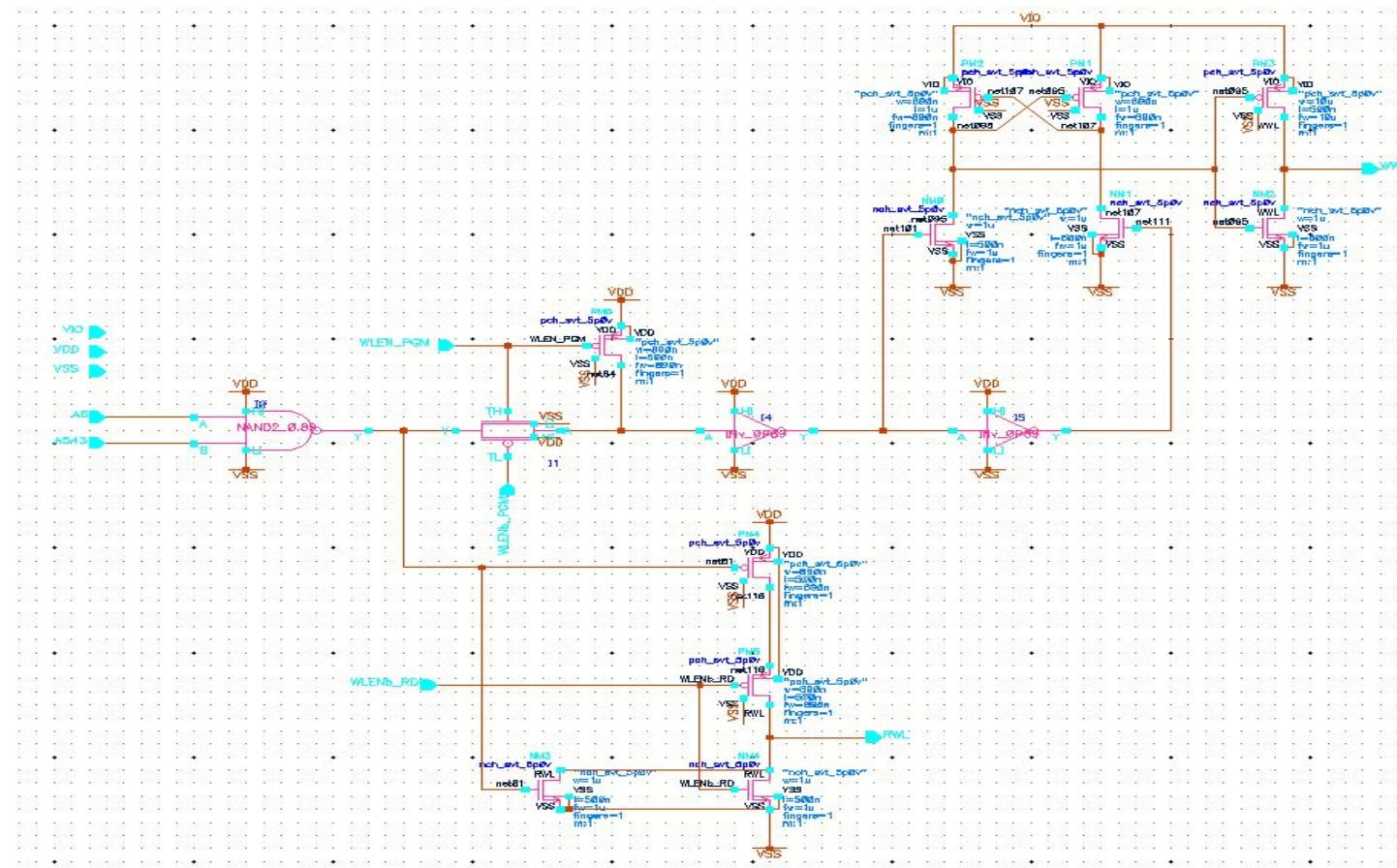


SL_Driver
_8C_Schematic



SL_Driver_Schematic

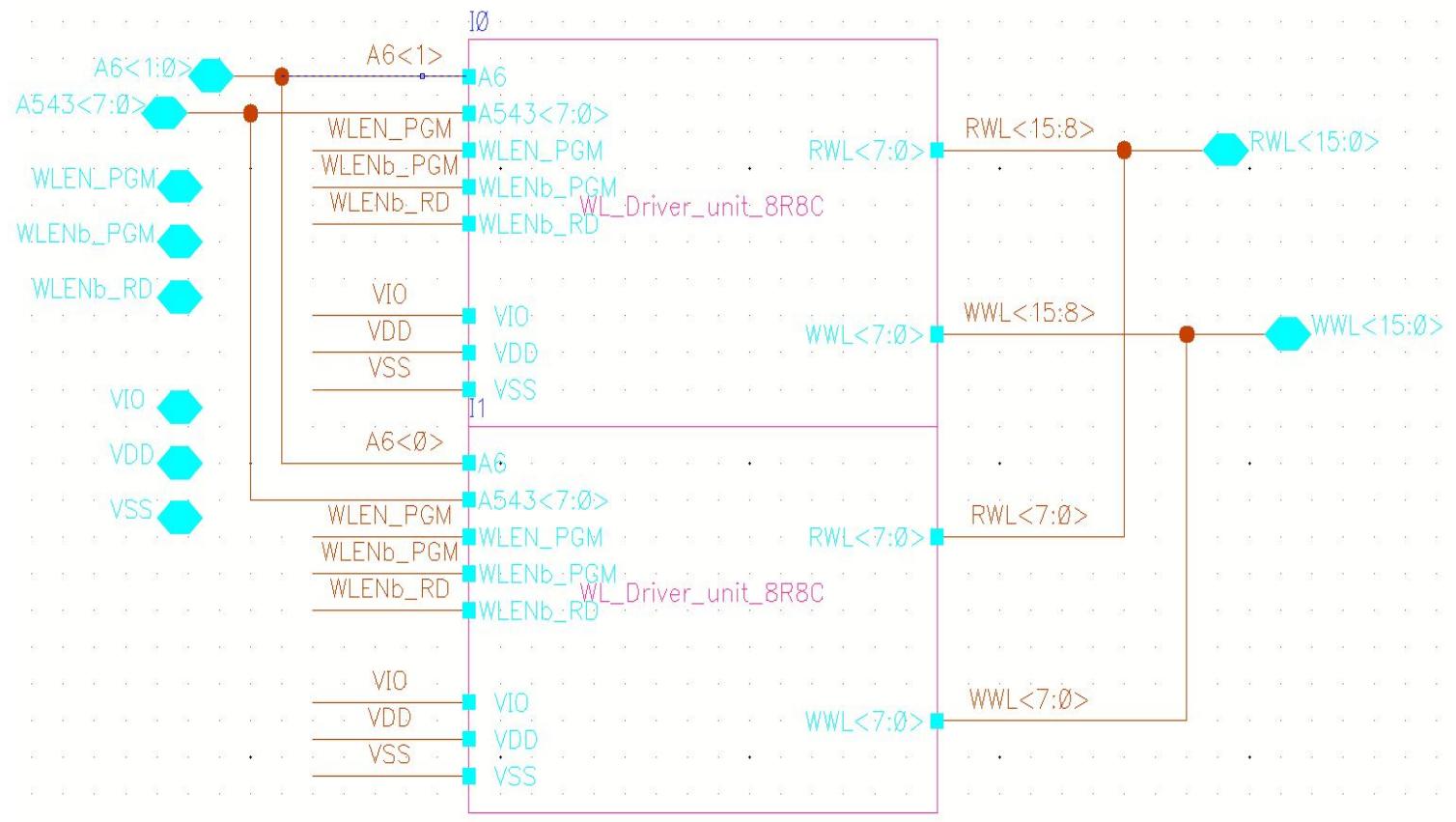
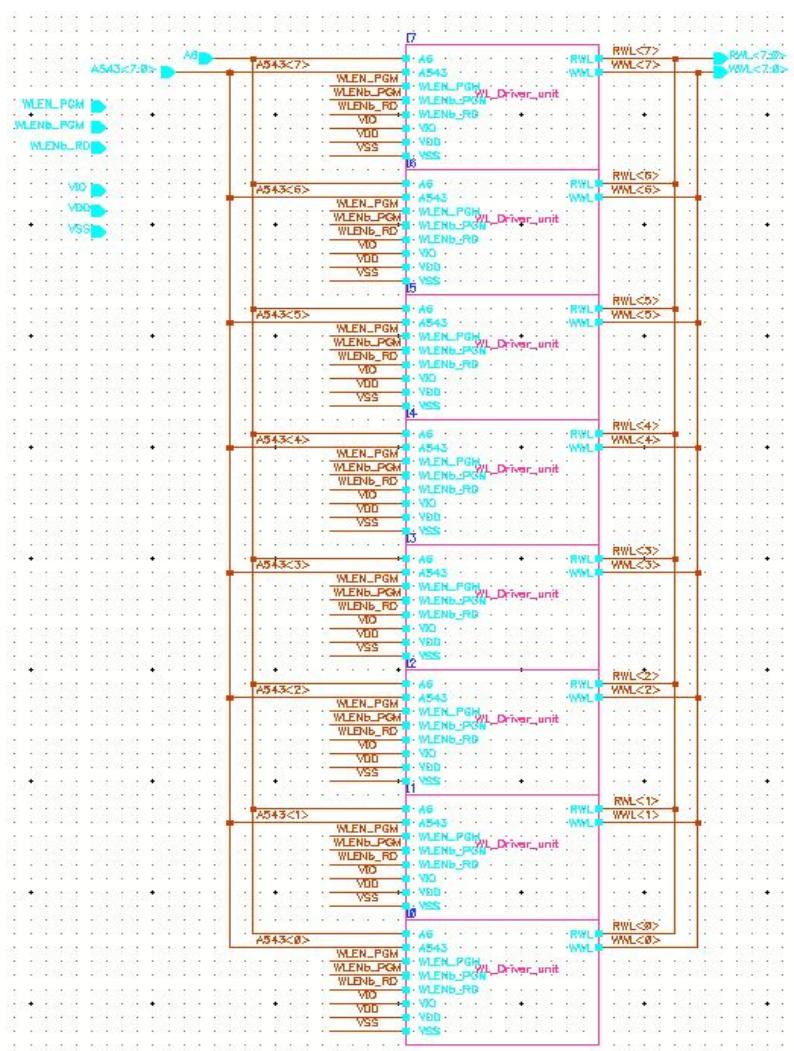
DBHitek 180nm BCD Process eFuse Cell Array _Simulation_Schematic



WL_Driver_Unit_Schematic

C

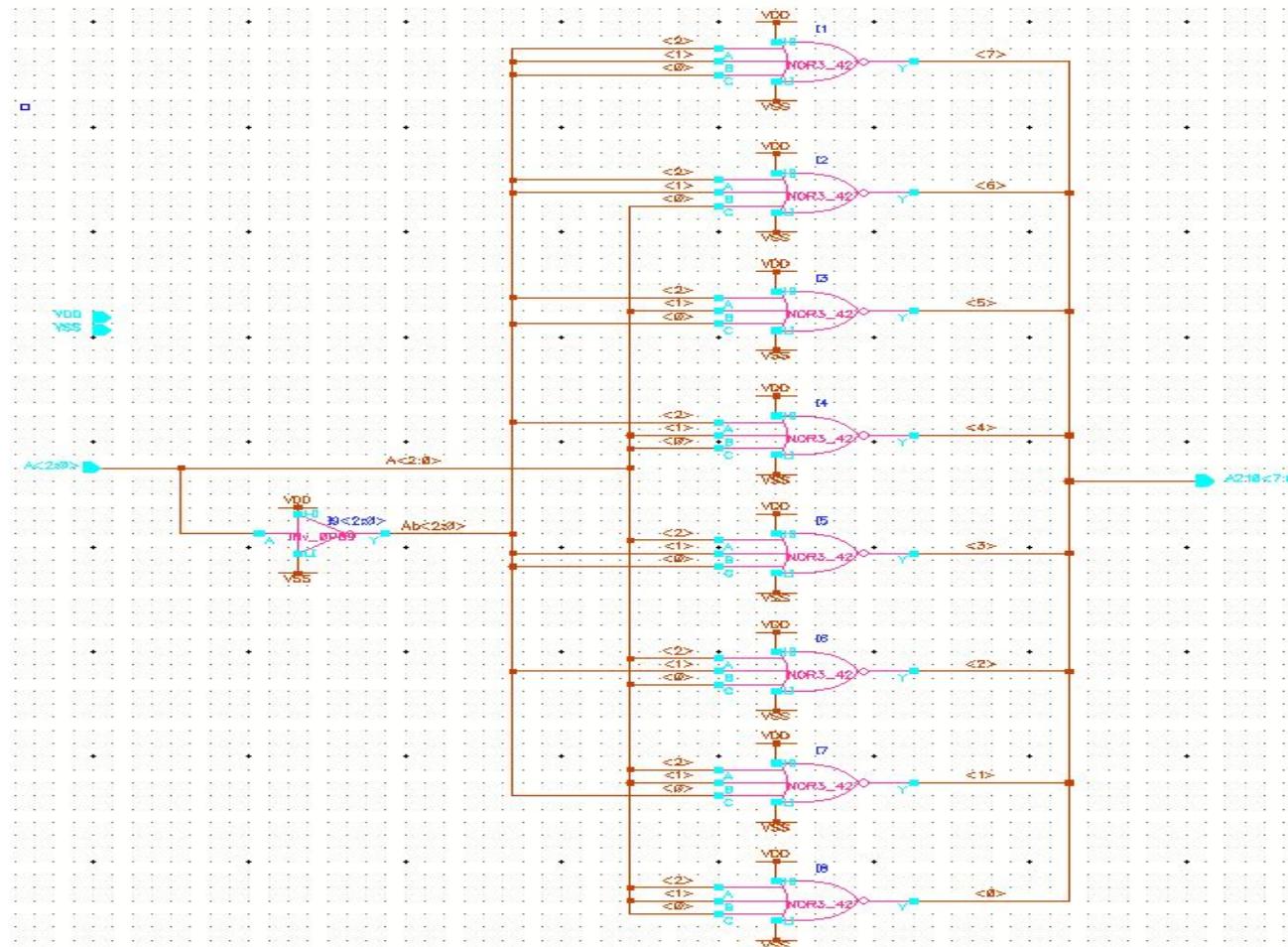
DBHitek 180nm BCD Process eFuse Cell Array _Simulation_Schematic



WL_Driver_Unit_1R8C

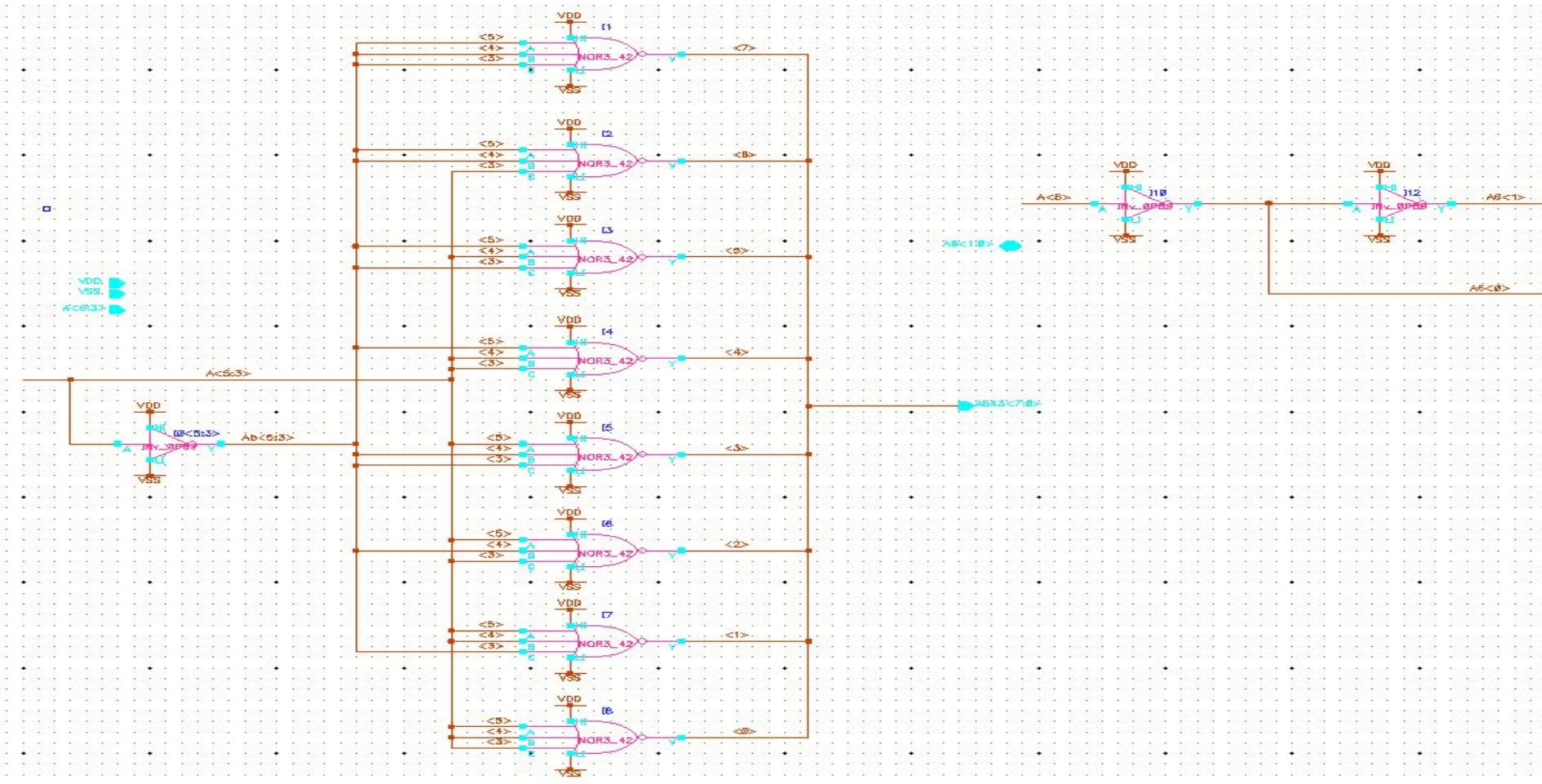
WL_Driver_Unit_8R8C

DBHitek 180nm BCD Process eFuse Cell Array _Simulation_Schematic



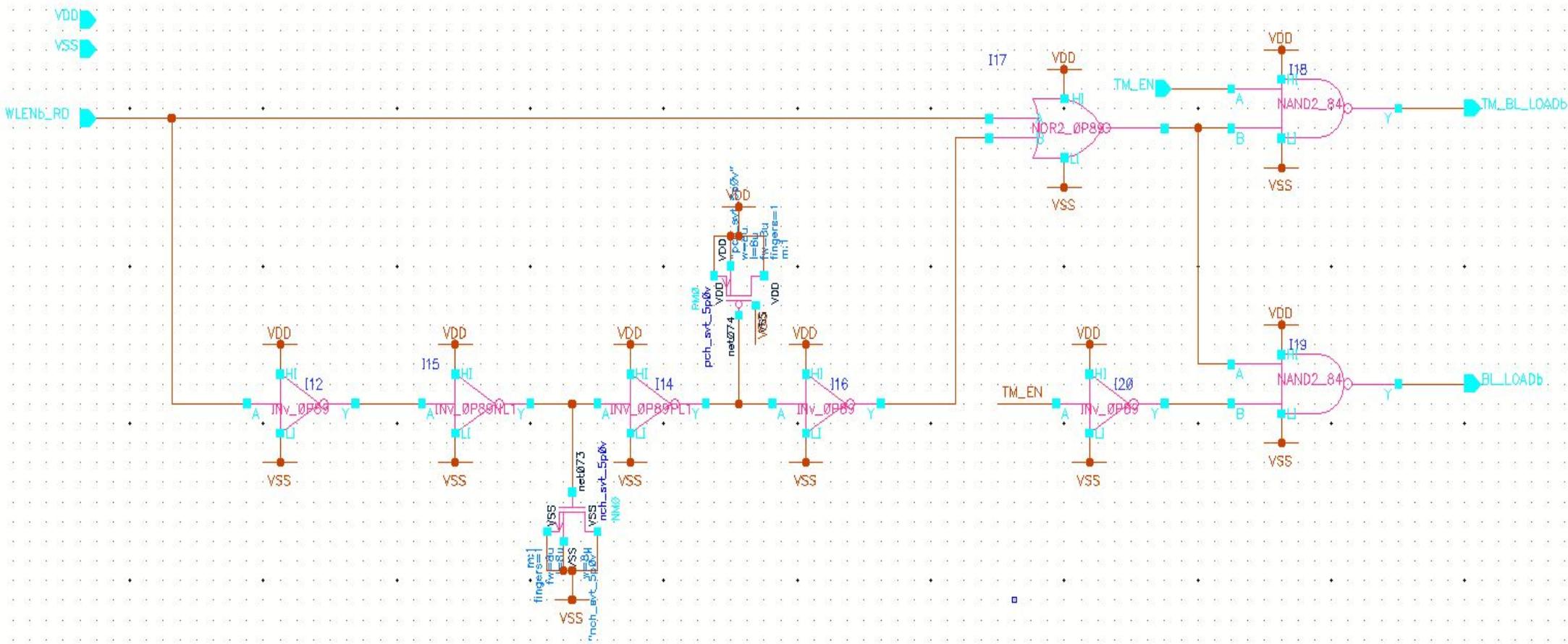
Ypre_Decoder_Schematic
C

DBHitek 180nm BCD Process eFuse Cell Array _Simulation_Schematic



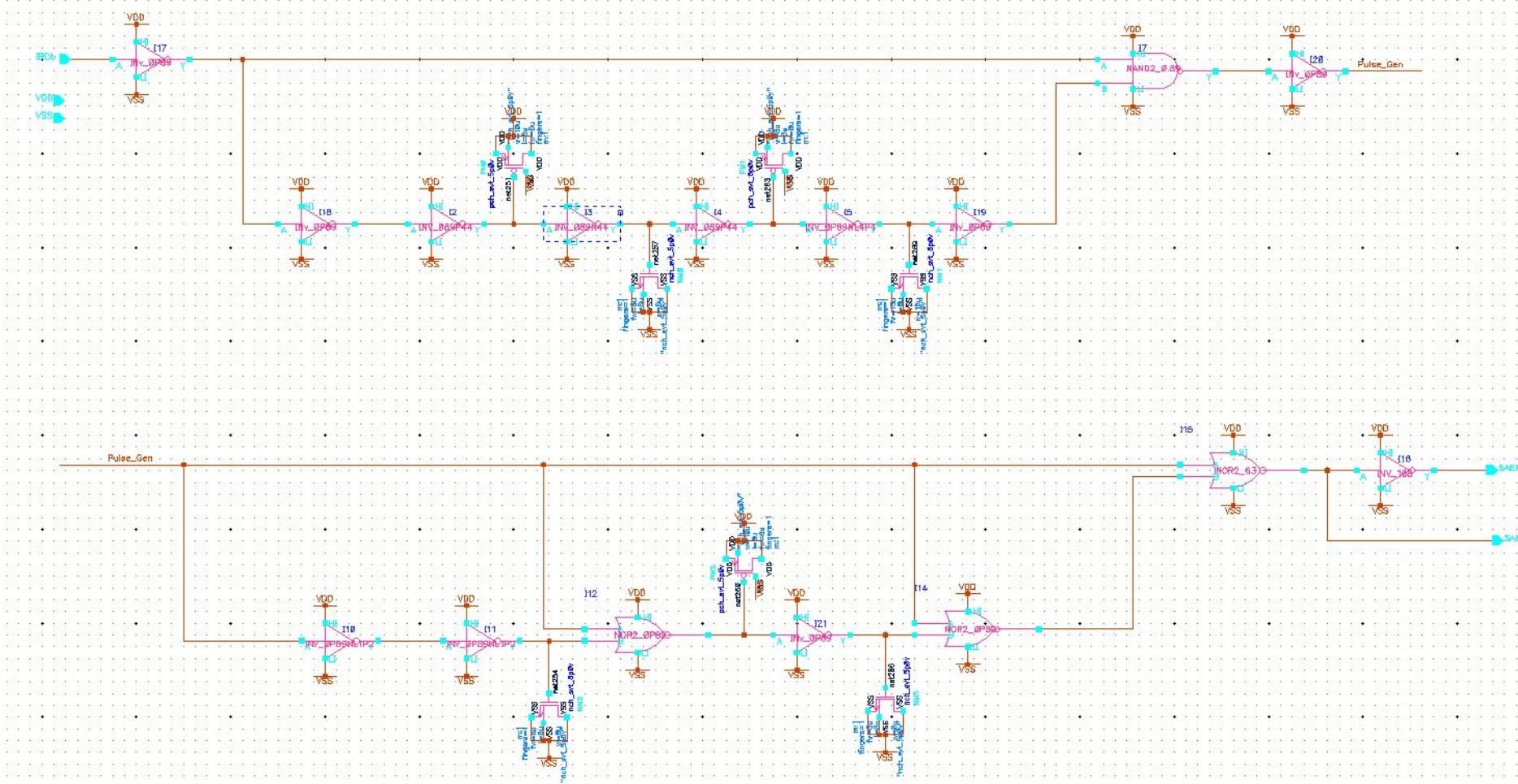
Xpre_Decoder_Schematic
C

DBHitek 180nm BCD Process eFuse Cell Array _Simulation_Schematic



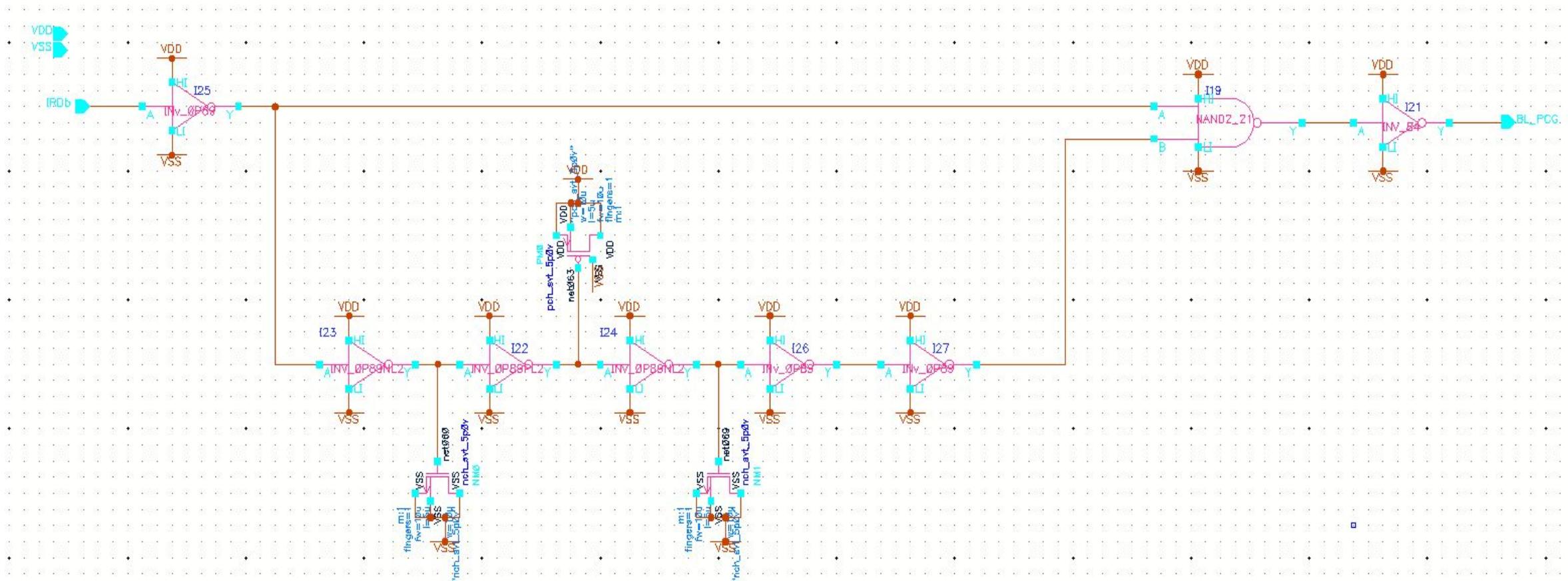
BL_Loadb_Schematic
C

DBHitek 180nm BCD Process eFuse Cell Array _Simulation_Schematic



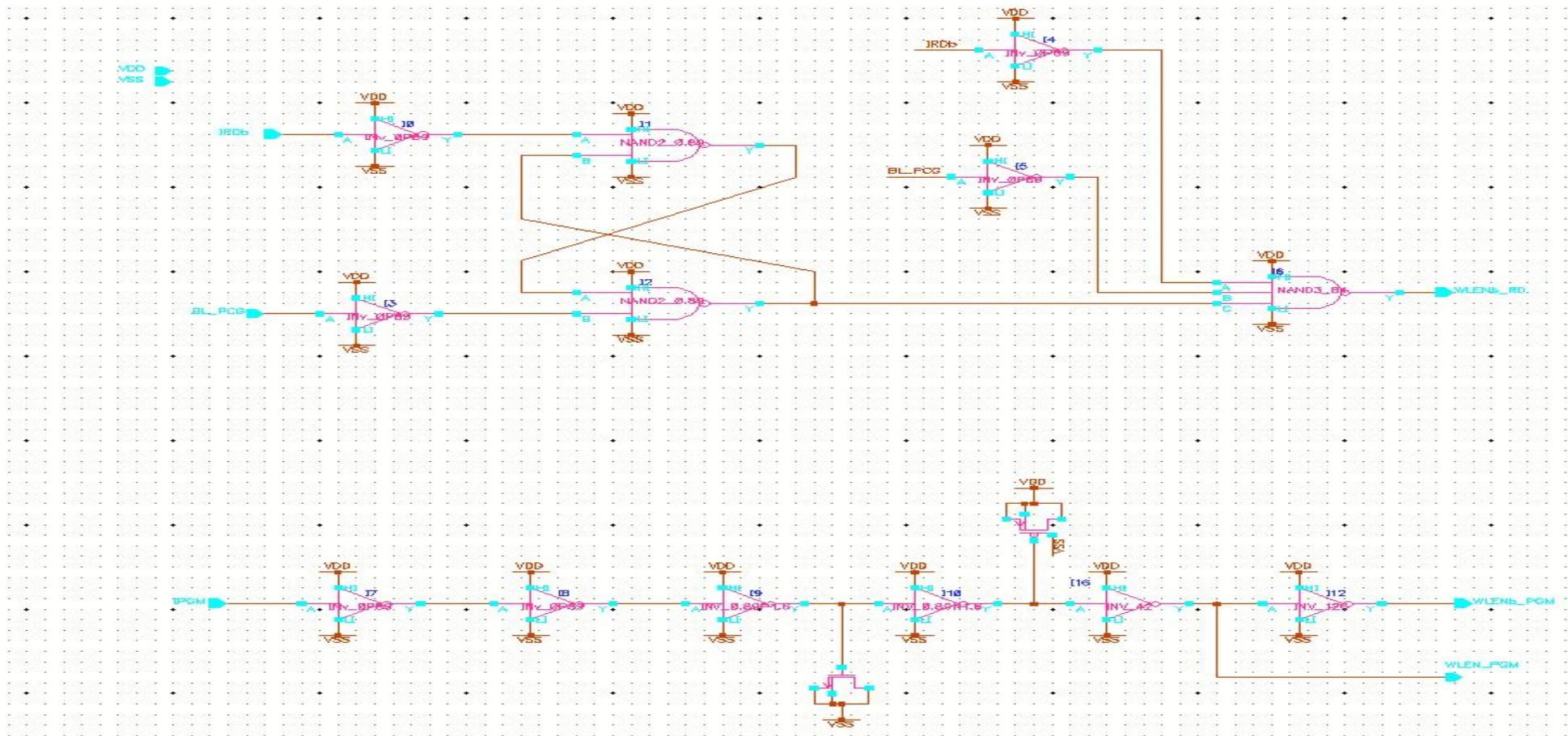
SAENb_Schematic

DBHitek 180nm BCD Process eFuse Cell Array _Simulation_Schematic



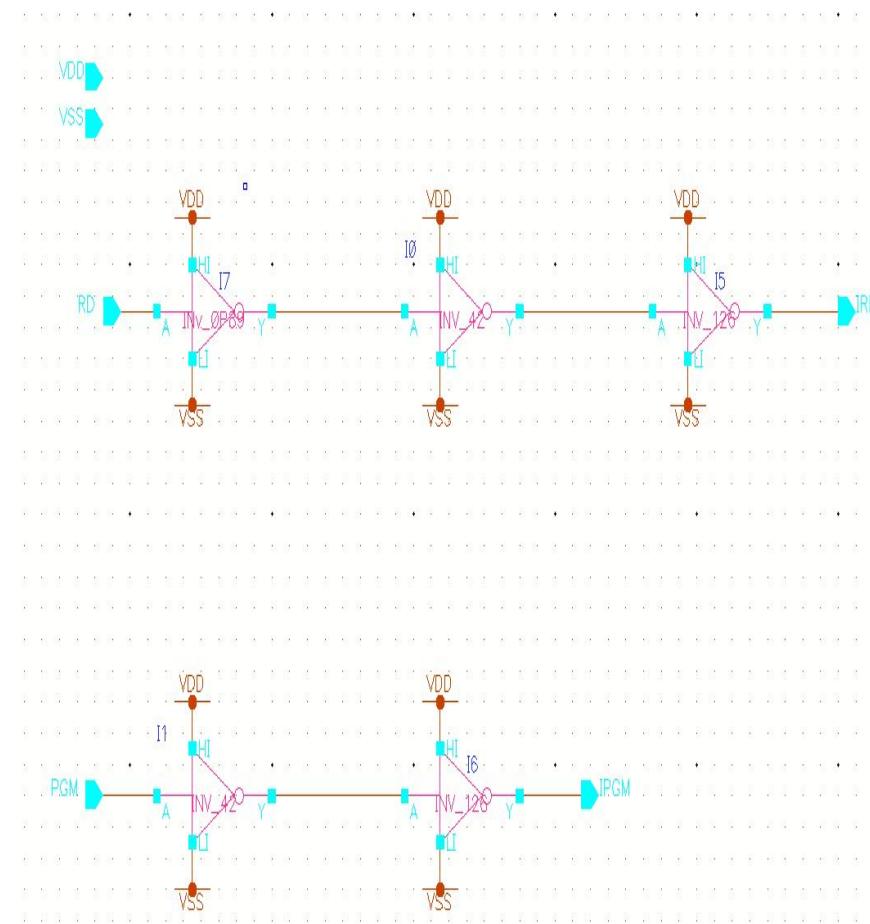
BL_PCG_Schematic

DBHitek 180nm BCD Process eFuse Cell Array _Simulation_Schematic



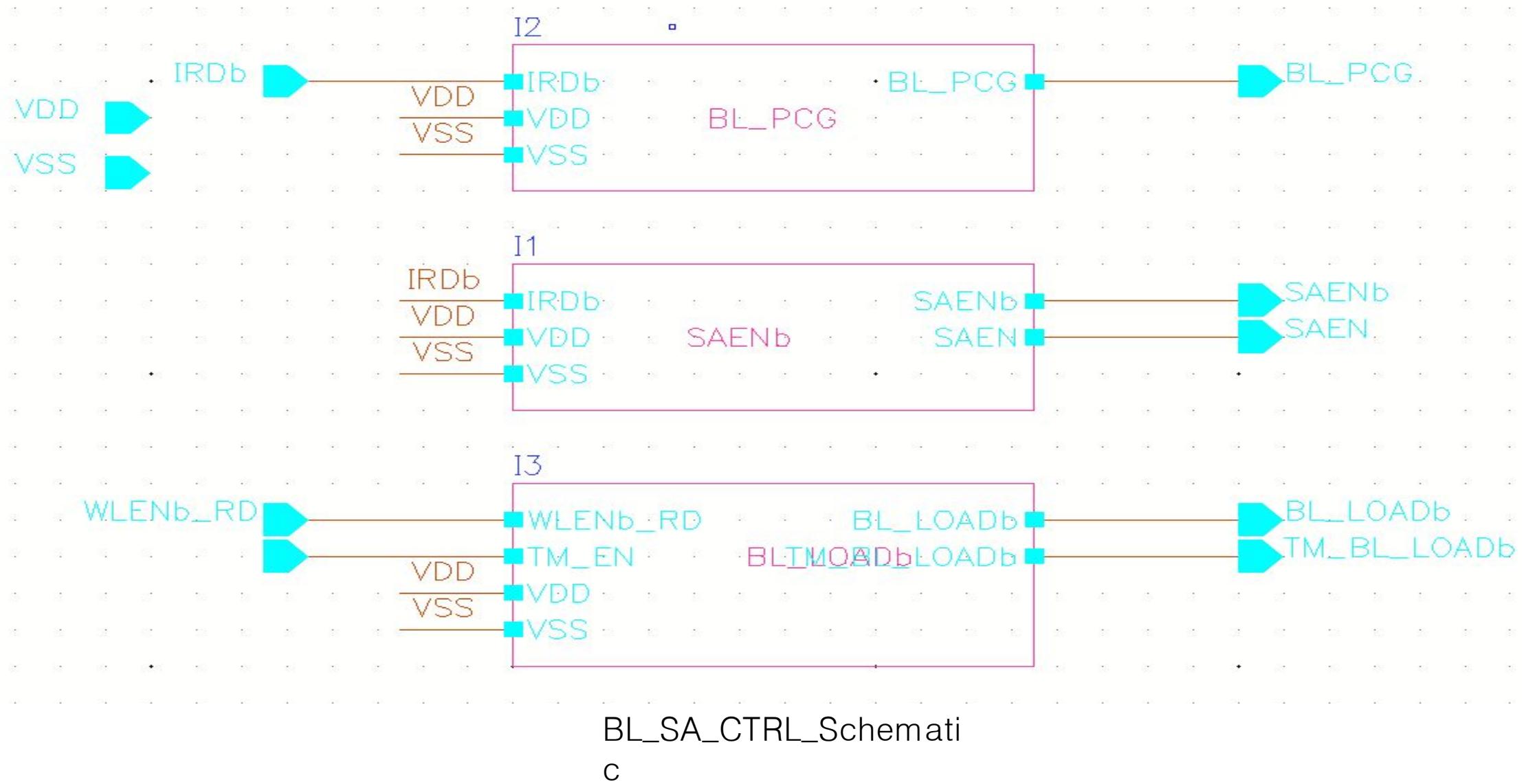
WL_CTRL_Schematic

DBHitek 180nm BCD Process eFuse Cell Array _Simulation_Schematic

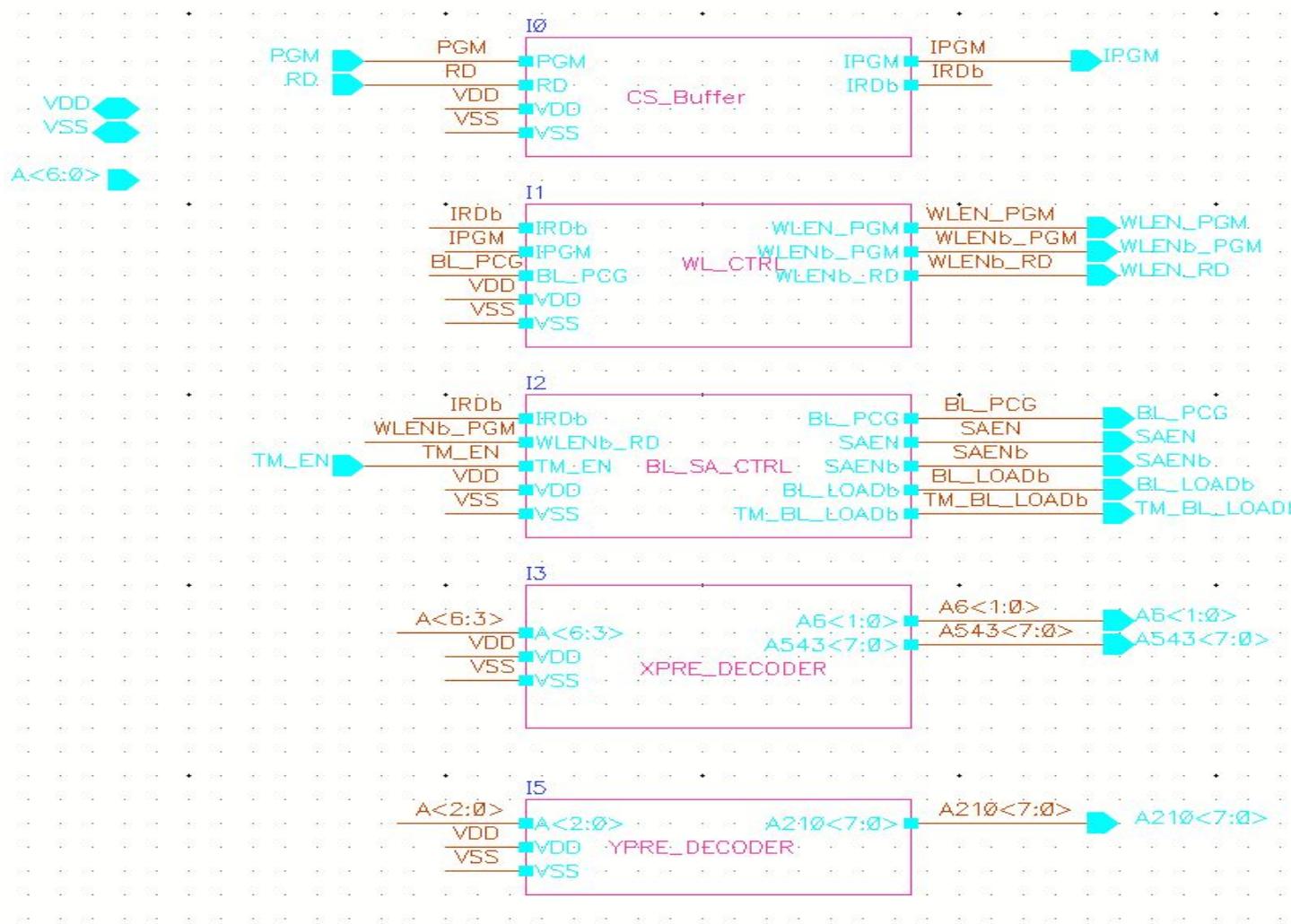


CS_Buffer_Schematic
C

DBHitek 180nm BCD Process
eFuse Cell Array _Simulation_Schematic

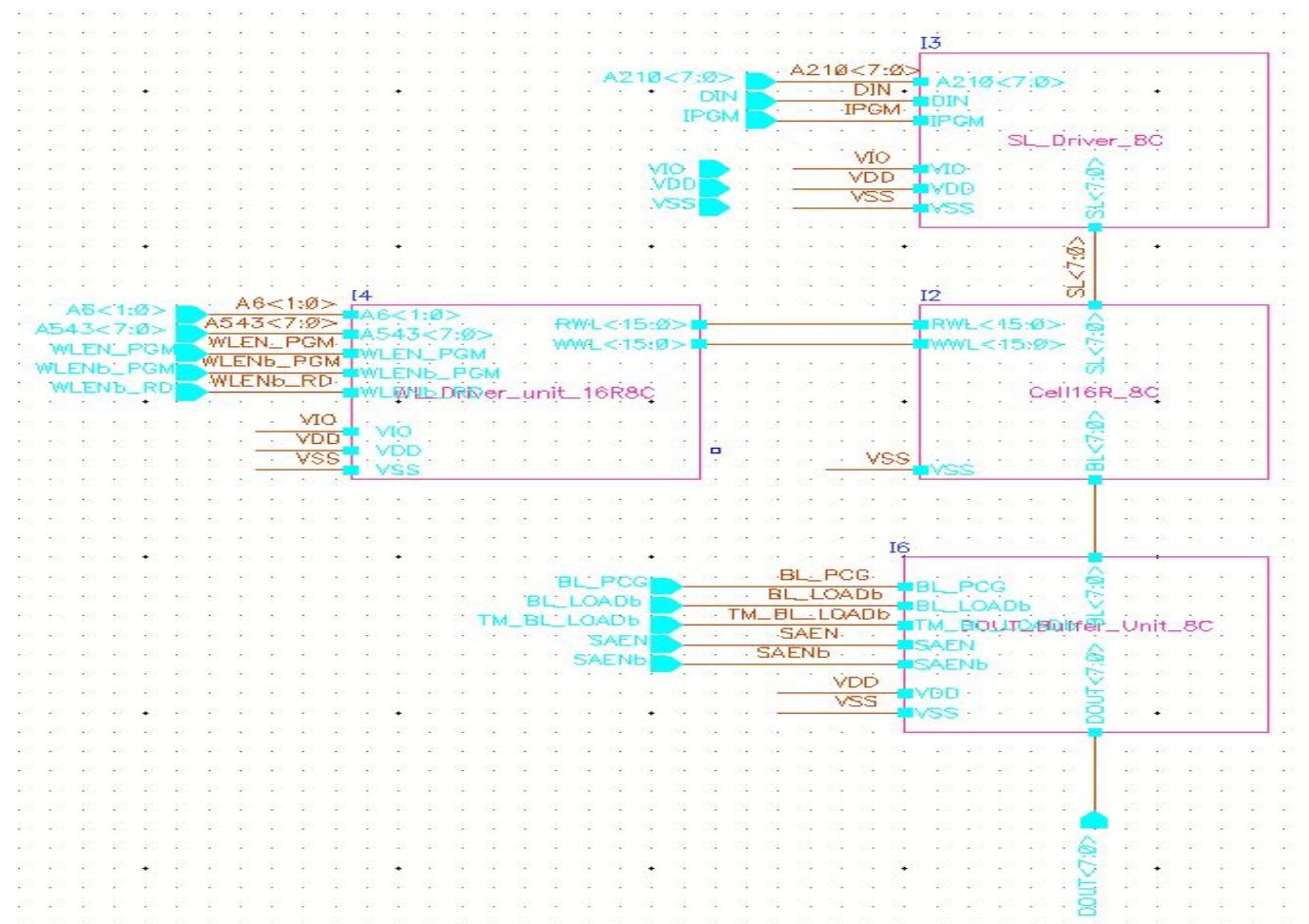


DBHitek 180nm BCD Process eFuse Cell Array _Simulation_Schematic



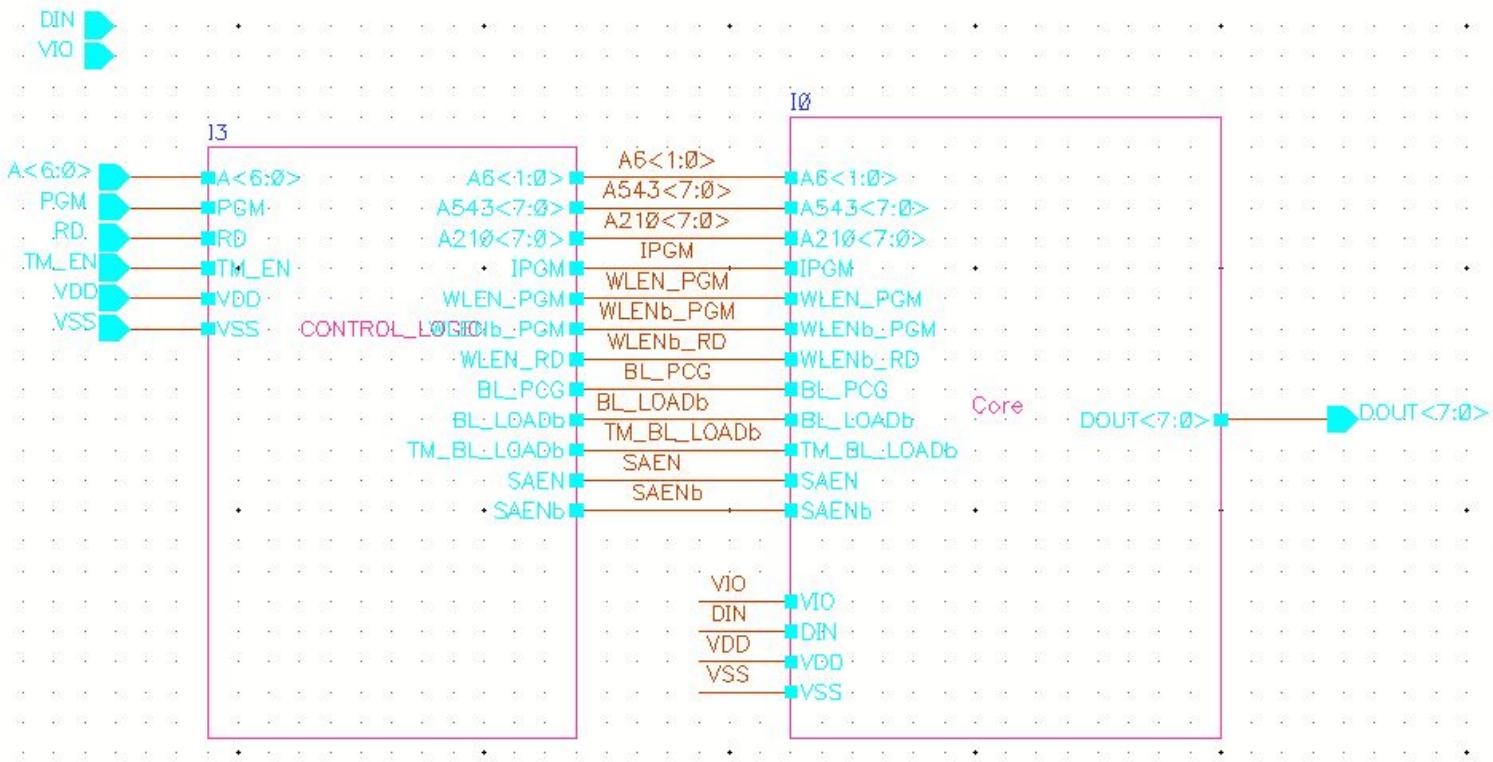
Control_Logic_Schematic

DBHitek 180nm BCD Process eFuse Cell Array _Simulation_Schematic



Core_Schematic

DBHitek 180nm BCD Process eFuse Cell Array _Simulation_Schematic



Top_Schematic

DBHitek 180nm BCD Process

eFuse Cell Array _Simulation_Schematic

Subject:128bit eFuse OTP IP design

□ **Problem statement**:creating a convenable circuit that satisfied these specifications

– Supply voltage: VDD=2.2V – VIO=5.5V Temperature: -40C 25 C to 125C

□ **Operating Mode** : Program/Program Verify–Read/ReadProgram.

– ReadProgram Verify:10k

– Read Mode :5k {Read_Programmed Cell& Read_Uprogrammed Cell}

– Current :<100uA. (Decreasing current from 168.4uA to 100uA)

□ **Expected result:** Suitable block diagram have to be find out by modifying the above simulation circuits based on the requirements.

DBHitek 180nm BCD Process
eFuse Cell Array _Simulation_Schematic

Simulation software :[CX-HSPUI -Xftp5 -Crimson Editor](#)

Design & Layout software :[VLSI7\(VLSI7:177\) -Xmanager5\[:0.0\]](#)



DBHitek 180nm BCD Process
eFuse Cell Array _Simulation_Schematic

eFuse OTP

VDD	Temp	Program Verify Read Mode					Read Mode				
		R _S model	R _F model	T _I model	T _S model	T _V model	R _S model	R _F model	T _I model	T _S model	T _V model
4.5V	-40°C	7.2K	6.1K	7.3K	7.6K	6.5K	3.1K	3.3K	3.7K	4.1K	3.8K
	25°C	9.1K	8.6K	8.9K	9.2K	9.4K	4.3K	4.6K	4.9K	4.8K	4.8K
	125°C	10K	9.3K	9.7K	9.9K	9K	3.9K	4.3K	4.6K	5K	4.8K
5V	-40°C	5.5K	5.6K	6K	6.2K	5.9K	1.9K	2.6K	2.8K	3K*	3.1K
	25°C	7.1K	7.2K	7.3K	7.7K	7K	2.9K	3.4K	3.7K	3.9K	3.9K
	125°C	7.6K	7.7K	7.9K	8.1K	7.4K	2.6K	3.2K	3.4K	3.7K	3.7K
5.5V	-40°C	4.4K	4.1K	5K	5.2K	5.1K	0.9K	1.5K	2.1K	2.2K	2.6K
	25°C	5.9K	6.2K	6.3K	6.5K	6.3K	2K	2.7K	3K	3.1K	3.3K
	125°C	6.1K	6.5K	6.6K	6.7K	6.5K	1.4K	2.4K	2.6K	2.7K	2.8K